



BU208A BU508A/BU508AFI

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTORS

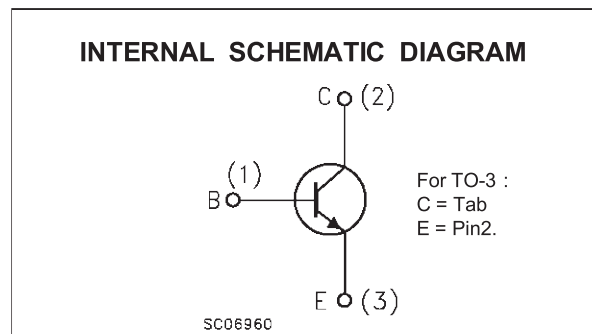
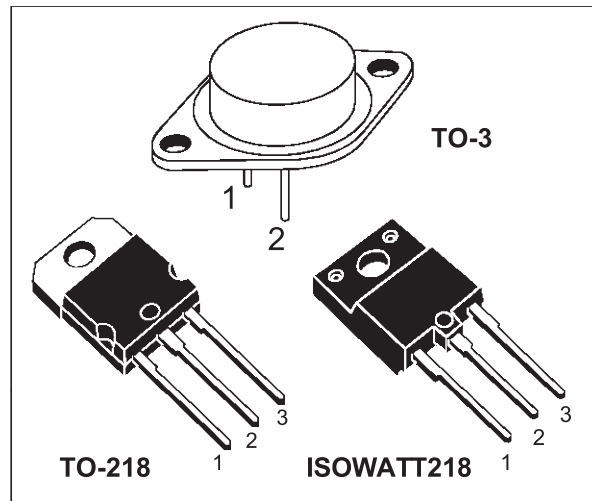
- STMicroelectronics PREFERRED SALESTYPES
- HIGH VOLTAGE CAPABILITY
- U.L. RECOGNISED ISOWATT218 PACKAGE (U.L. FILE # E81734 (N))
- JEDEC TO-3 METAL CASE.

APPLICATIONS:

- HORIZONTAL DEFLECTION FOR COLOUR TV

DESCRIPTION

The BU208A, BU508A and BU508AFI are manufactured using Multi-epitaxial Mesa technology for cost-effective high performance and use a Hollow Emitter structure to enhance switching speeds.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value			Unit
		TO - 3	TO - 218	ISOWATT218	
V_{CES}	Collector-Emitter Voltage ($V_{BE} = 0$)	1500			V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	700			V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	10			V
I_C	Collector Current	8			A
I_{CM}	Collector Peak Current ($t_p < 5$ ms)	15			A
P_{tot}	Total Dissipation at $T_c = 25$ °C	150	125	50	W
T_{stg}	Storage Temperature	-65 to 175	-65 to 150	-65 to 150	°C
T_j	Max. Operating Junction Temperature	175	150	150	°C

THERMAL DATA

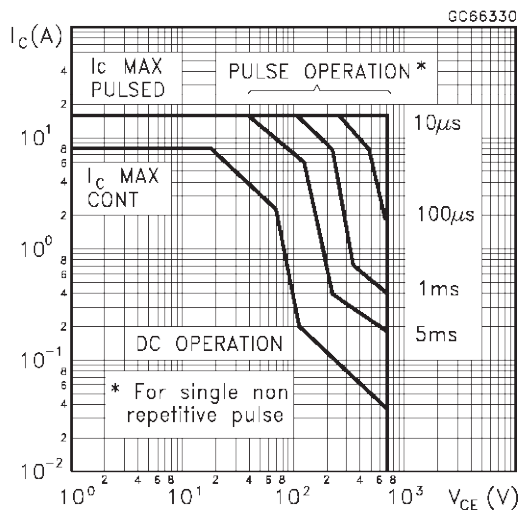
			TO-3	TO-218	ISOWATT218	
R _{thj-case}	Thermal Resistance Junction-case	Max	1	1	2.5	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

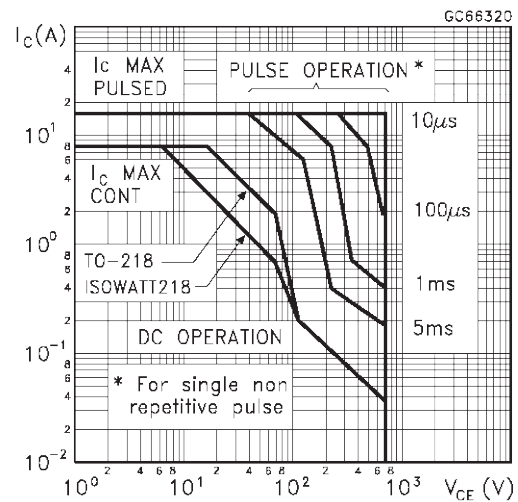
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 1500 V V _{CE} = 1500 V			1 2	mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			100	μA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA	700			V
V _{EBO}	Emitter Base Voltage (I _C = 0)	I _E = 10 mA	10			V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 4.5 A I _B = 2 A			1	V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	I _C = 4.5 A I _B = 2 A			1.3	V
t _s t _f	INDUCTIVE LOAD Storage Time Fall Time	I _C = 4.5 A h _{FE} = 2.5 V _{CC} = 140 V L _C = 0.9 mH L _B = 3 μH		7 0.55		μs μs
f _T	Transition Frequency	I _C = 0.1 A V _{CE} = 5 V f = 5 MHz		7		MHz

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

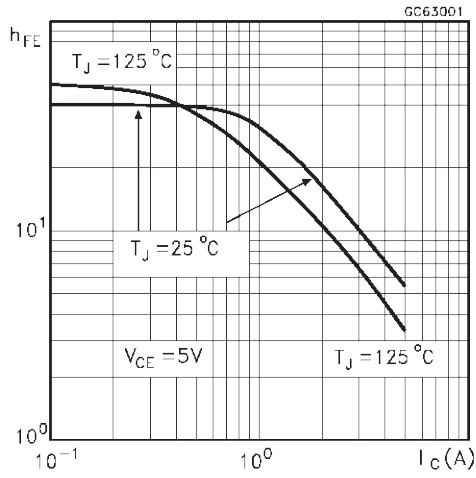
Safe Operating Area (TO-3)



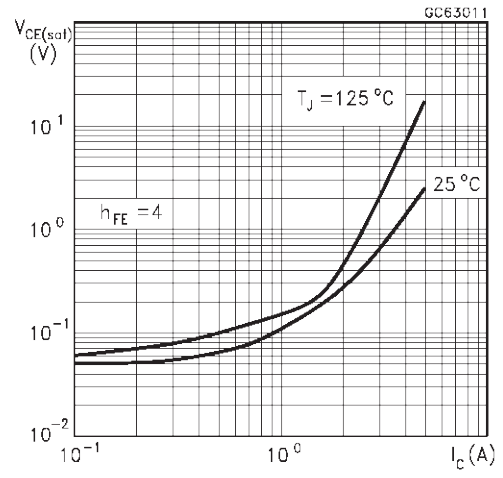
Safe Operating Areas (TO-218/ISOWATT218)



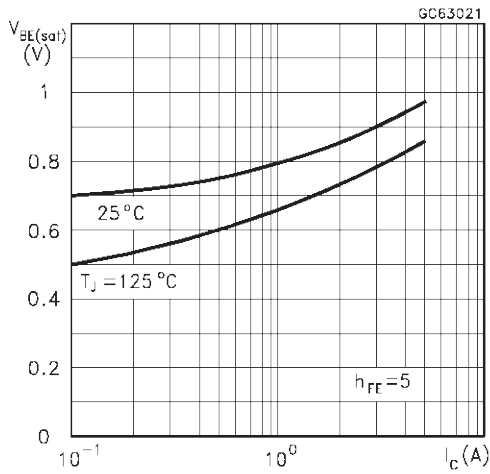
DC Current Gain



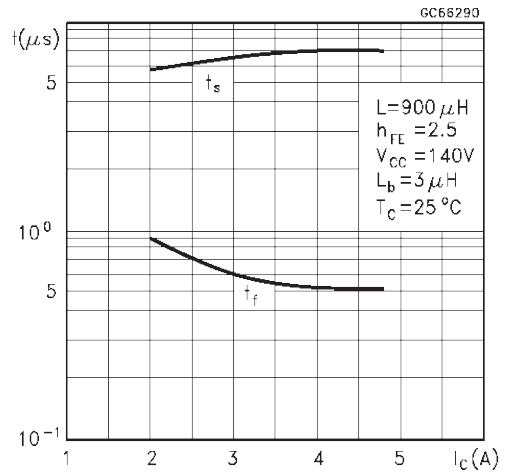
Collector Emitter Saturation Voltage



Base Emitter Saturation Voltage



Switching Time Inductive Load



Switching Time Inductive Load (see figure 1)

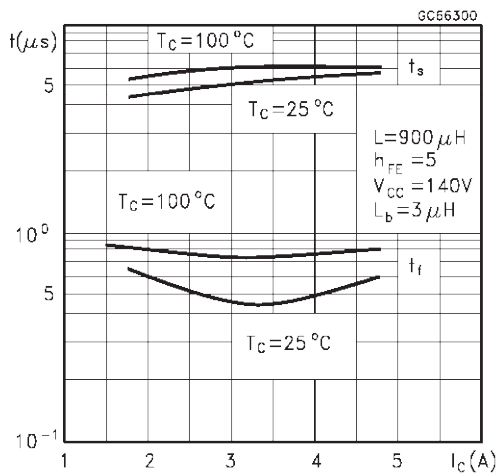
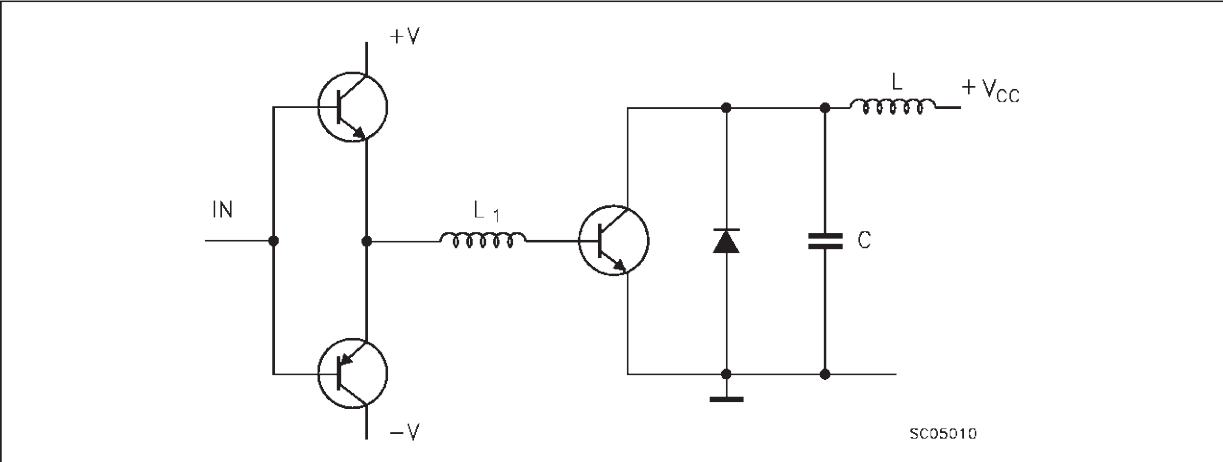
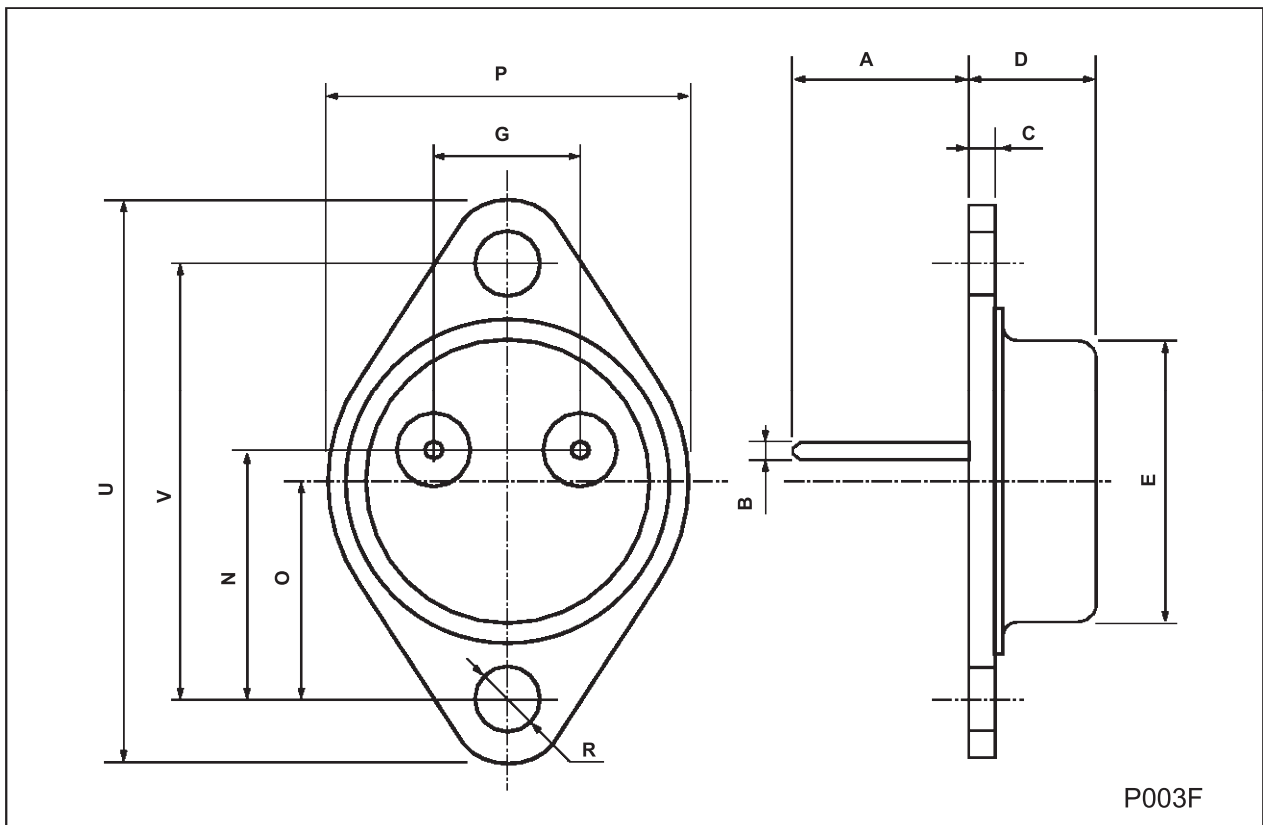


Figure 1: Inductive Load Switching Test Circuit.



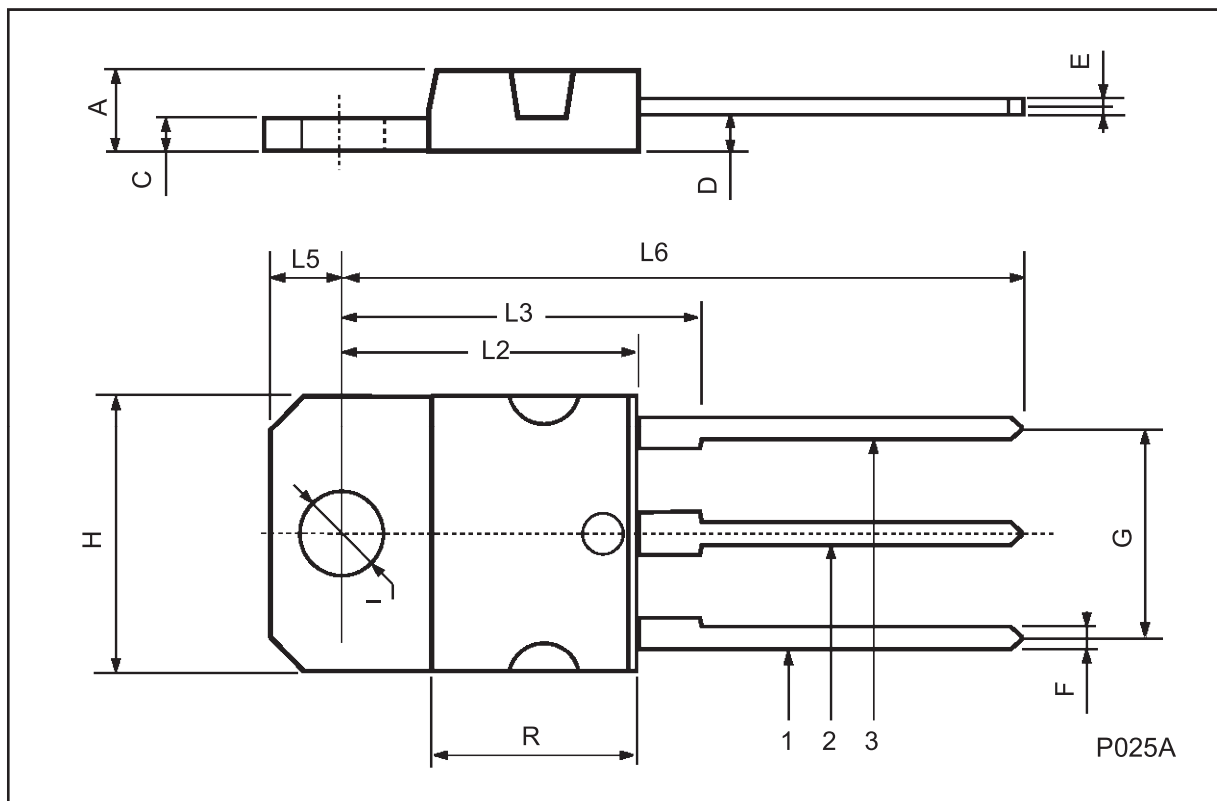
TO-3 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.00		13.10	0.433		0.516
B	0.97		1.15	0.038		0.045
C	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
E	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
P	25.00		26.00	0.984		1.023
R	4.00		4.09	0.157		0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193



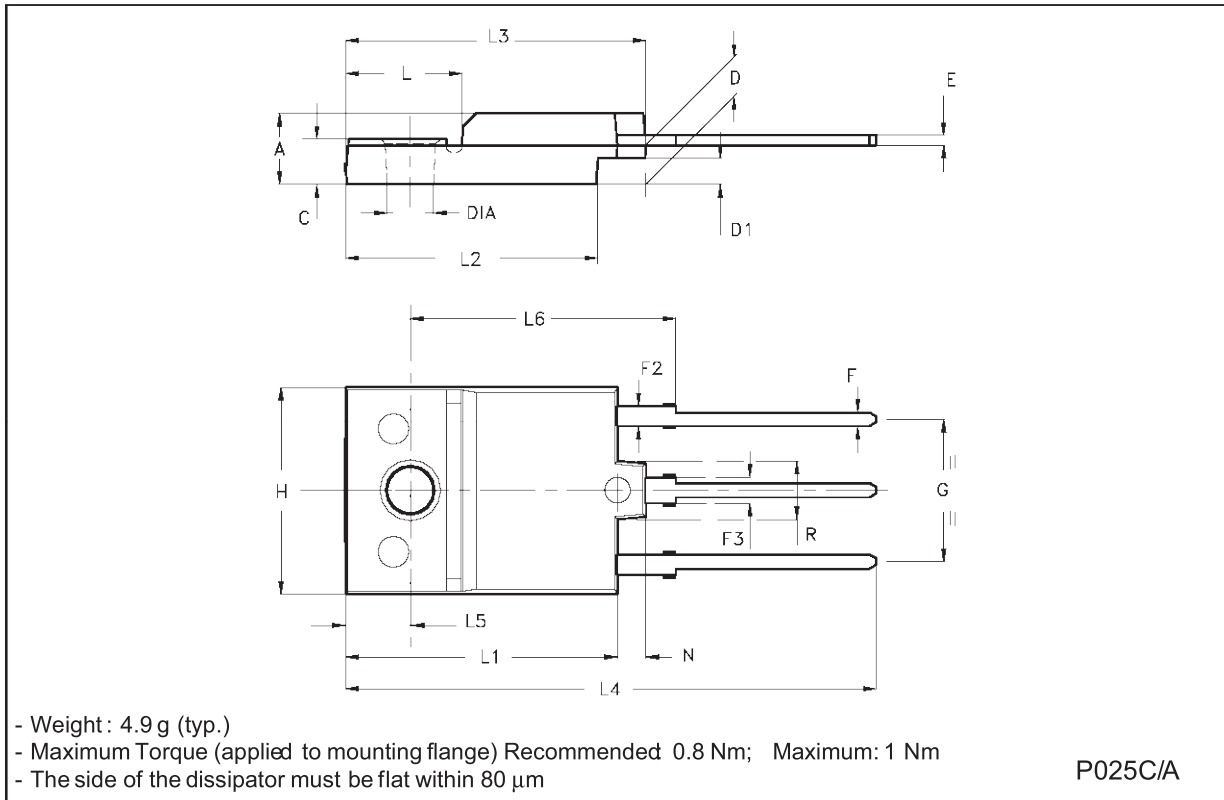
TO-218 (SOT-93) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		4.9	0.185		0.193
C	1.17		1.37	0.046		0.054
D		2.5			0.098	
E	0.5		0.78	0.019		0.030
F	1.1		1.3	0.043		0.051
G	10.8		11.1	0.425		0.437
H	14.7		15.2	0.578		0.598
L2	-		16.2	-		0.637
L3		18			0.708	
L5	3.95		4.15	0.155		0.163
L6		31			1.220	
R	-		12.2	-		0.480
Ø	4		4.1	0.157		0.161



ISOWATT218 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.35		5.65	0.211		0.222
C	3.30		3.80	0.130		0.150
D	2.90		3.10	0.114		0.122
D1	1.88		2.08	0.074		0.082
E	0.75		0.95	0.030		0.037
F	1.05		1.25	0.041		0.049
F2	1.50		1.70	0.059		0.067
F3	1.90		2.10	0.075		0.083
G	10.80		11.20	0.425		0.441
H	15.80		16.20	0.622		0.638
L		9			0.354	
L1	20.80		21.20	0.819		0.835
L2	19.10		19.90	0.752		0.783
L3	22.80		23.60	0.898		0.929
L4	40.50		42.50	1.594		1.673
L5	4.85		5.25	0.191		0.207
L6	20.25		20.75	0.797		0.817
N	2.1		2.3	0.083		0.091
R		4.6			0.181	
DIA	3.5		3.7	0.138		0.146



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